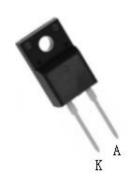
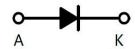


FRED Ultrafast Soft Recovery Diode, 15A

Features:

- Ultrafast Recovery
- 175°C operating junction temperature
- High frequency operation
- Low power loss, less RFI and EMI
- Low I_R value
- High surge capacity
- Epitaxial chip construction





Product Summary	
VR	1200 V
lf(AV)	15A
trr	32 ns

Description/Applications

These diodes are optimized to less losses and EMI/RFI in high frequency power conditioning system. The soft recovery behavior of the diodes offers the need as snubber in most applications. These devices are ideally suited for HF welding power converters and other applications where the switching losses are not significant portion of the total losses.

Absolute Maximum Ratings				
Parameter	Symbol	Test Conditions	Values	Units
Repetitive peak reverse voltage	Vrrm		1200	V
Continuous forward current	lf(AV)	Tc =110°C	15	
Single pulse forward current	IFSM	Tc =25°C	120	А
Maximum repetitive forward current	IFRM	Square wave, 20kHZ	30	
Operating junction	Тј		175	°C
Storage temperatures	Tstg		-55 to +175	°C

www.hsmsemi.com 1/3



Electrical characteristics (Ta=25°C unless otherwise specified)						
Parameter	Symbol	Test Conditions	Min	Тур.	Max.	Units
Breakdown voltage Blocking voltage	VBR, V _R	Ir=100µA	1200			
Forward voltage	VF	IF=15A		1.8	2.50	V
(Per Diode)		IF=15A, Tj =125°C		1.5	2.30	
Reverse leakage	IR	Vr= Vrrm			20	μД
current(Per Diode)		Tj=150°C, Vr=600V			200	
Reverse recovery	trr	I _F =0.5A, I _R =1A, I _{RR} =0.25A		50	60	ns
time(Per Diode)		$I_F=1A, V_R=30V, di/dt = 200A/us$		32	50	ns

Thermal characteristics

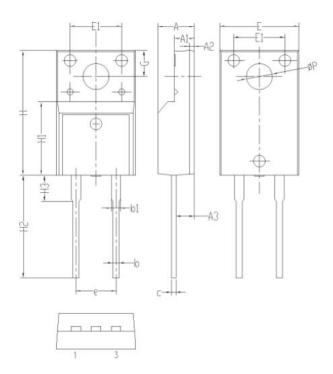
Paramter	Symbol	Тур	Units
Junction-to-Case	$R_{ heta JC}$	2.5	°C/W

www.hsmsemi.com 2/3



Package Information

TO-220F-2 PACKAGE



Symbol	Dimensions(millimeters)		
Syllibol	Min.	Max.	
Α	4.35	4.75	
A1	2.30	2.70	
A2	0.40	0.80	
A3	2.10	2.50	
b	0.60	1.00	
b1	1.00	1.40	
С	0.30	0.70	
е	4.60	5.40	
Е	9.80	10.2	
E1	6.30	6.70	
Η	15.6	16.0	
H1	8.80	9.20	
H2	12.9	13.5	
H3	3.10	3.50	
G	3.10	3.50	
ΦР	3.10	3.50	

www.hsmsemi.com 3/3